- 5. The method defined in claim 4 wherein said masking material is silicon dioxide.
  - 6. The method defined in claim 1 wherein said side-

walls of said narrow, shallow trenches are within about 5 degrees from the vertical.

7. The method defined in claim 1 wherein boron is implanted into the bottom surfaces of said narrow, deep
5 trenches prior to said thermally oxidizing step.